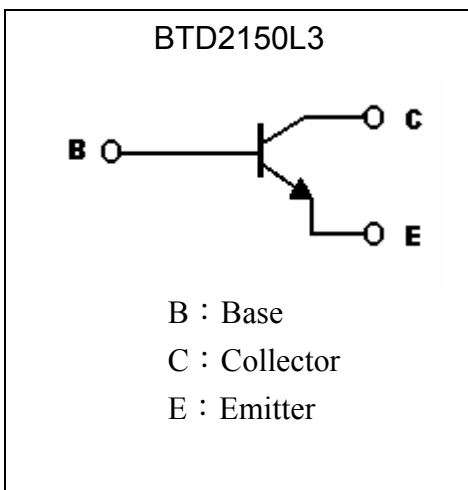
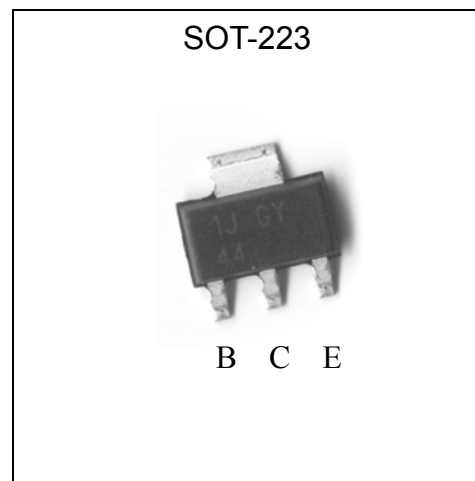


**Low Vcesat NPN Epitaxial Planar Transistor**

# BTD2150L3

**Features**

- Low  $V_{CE(sat)}$ ,  $V_{CE(sat)}=0.25\text{ V}$  (typical), at  $I_C / I_B = 2\text{ A} / 0.2\text{ A}$
- Excellent current gain characteristics
- Complementary to BTB1424L3

**Symbol**

**Outline**

**Absolute Maximum Ratings** ( $T_a=25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	3	A
Power Dissipation @ $T_c=25^\circ\text{C}$	$P_d$	5	W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55~+150	$^\circ\text{C}$



**Characteristics (Ta=25°C)**

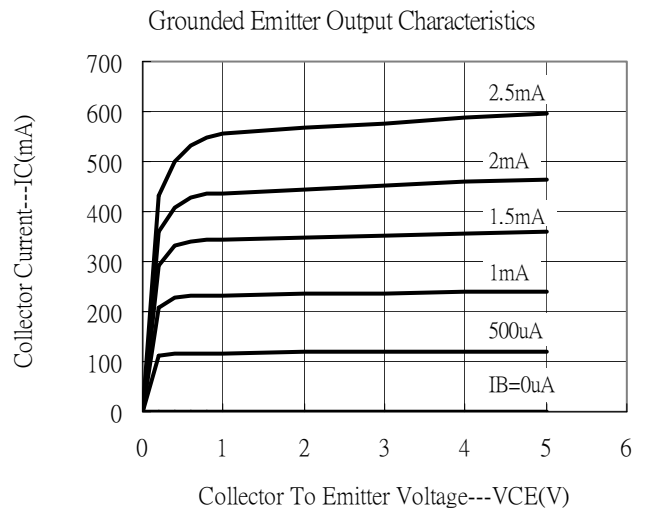
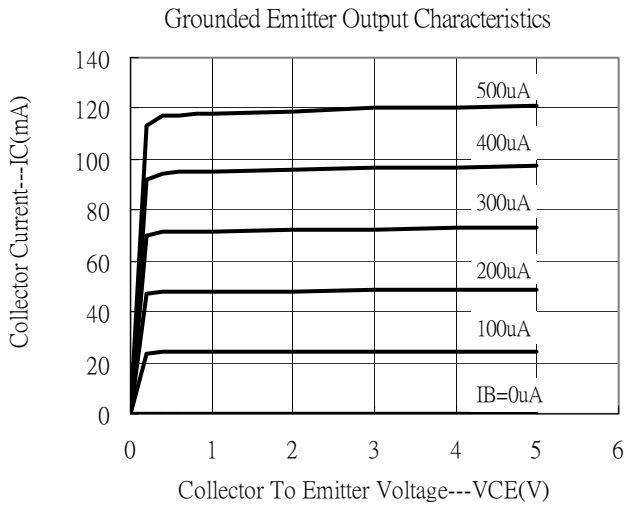
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
$BV_{CBO}$	40	-	-	V	$I_C=50\mu A, I_E=0$
$BV_{CEO}$	30	-	-	V	$I_C=1mA, I_B=0$
$BV_{EBO}$	5	-	-	V	$I_E=50\mu A, I_C=0$
$I_{CBO}$	-	-	100	nA	$V_{CB}=30V, I_E=0$
$I_{EBO}$	-	-	100	nA	$V_{EB}=3V, I_C=0$
* $V_{CE(sat)}$	-	0.25	0.5	V	$I_C=2A, I_B=0.2A$
* $V_{BE(sat)}$	-	-	1.5	V	$I_C=2A, I_B=0.2A$
* $h_{FE1}$	52	-	-	-	$V_{CE}=2V, I_C=20mA$
* $h_{FE2}$	82	-	560	-	$V_{CE}=2V, I_C=0.1A$
* $h_{FE3}$	50	-	-	-	$V_{CE}=3V, I_C=1A$
$f_t$	-	90	-	MHz	$V_{CE}=5V, I_C=0.1A, f=100MHz$
Cob	-	45	-	pF	$V_{CB}=10V, f=1MHz$

\*Pulse Test : Pulse Width  $\leq 380\mu s$ , Duty Cycle  $\leq 2\%$

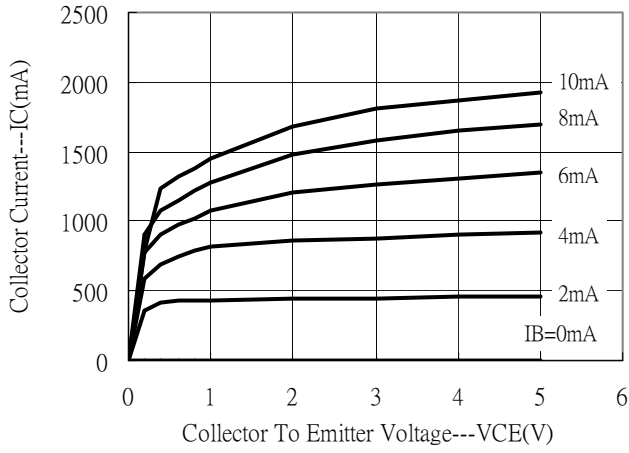
**Classification Of  $h_{FE} 2$**

Rank	P	Q	R	S
Range	82~180	120~270	180~390	270~560

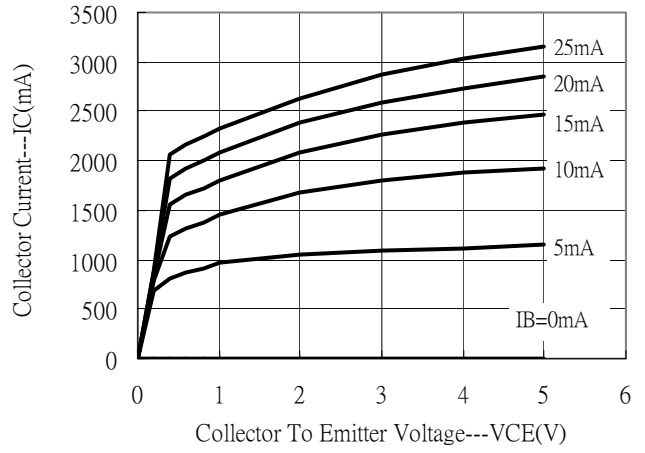
**Characteristic Curves**



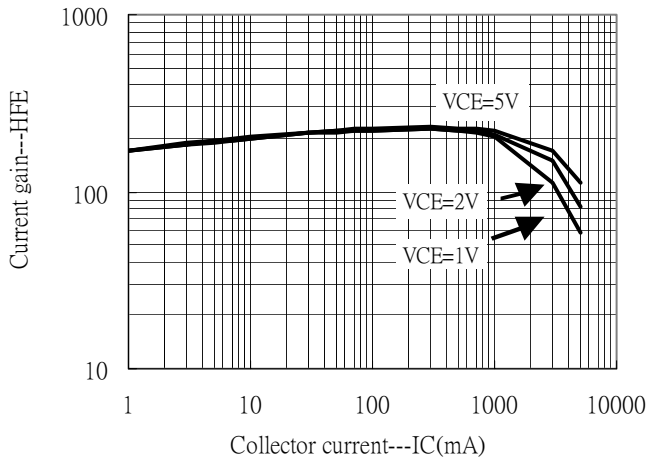
Grounded Emitter Output Characteristics



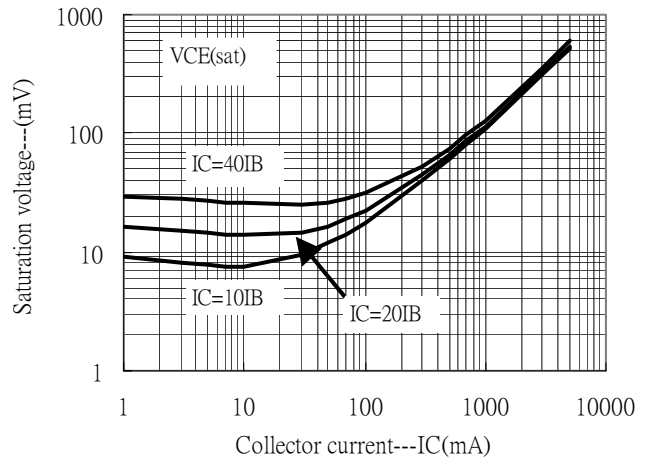
Grounded Emitter Output Characteristics



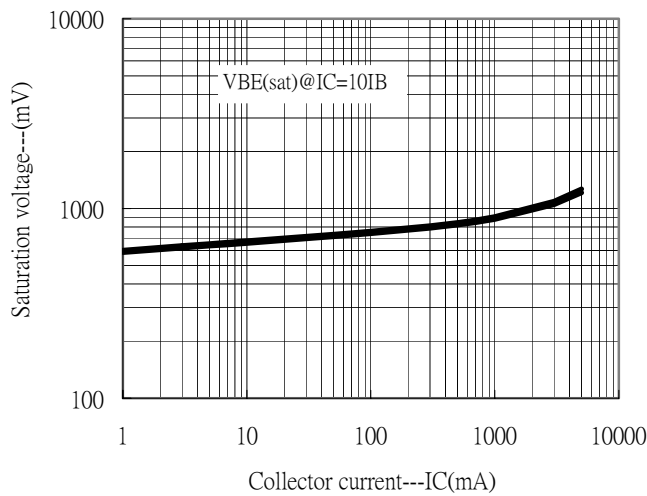
Current gain vs Collector current



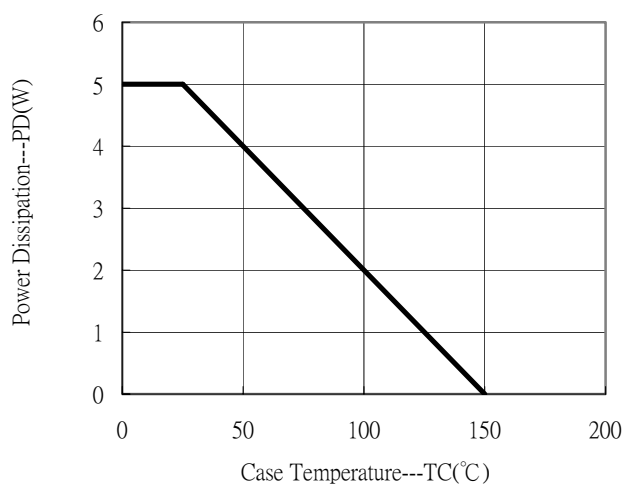
Saturation voltage vs Collector current



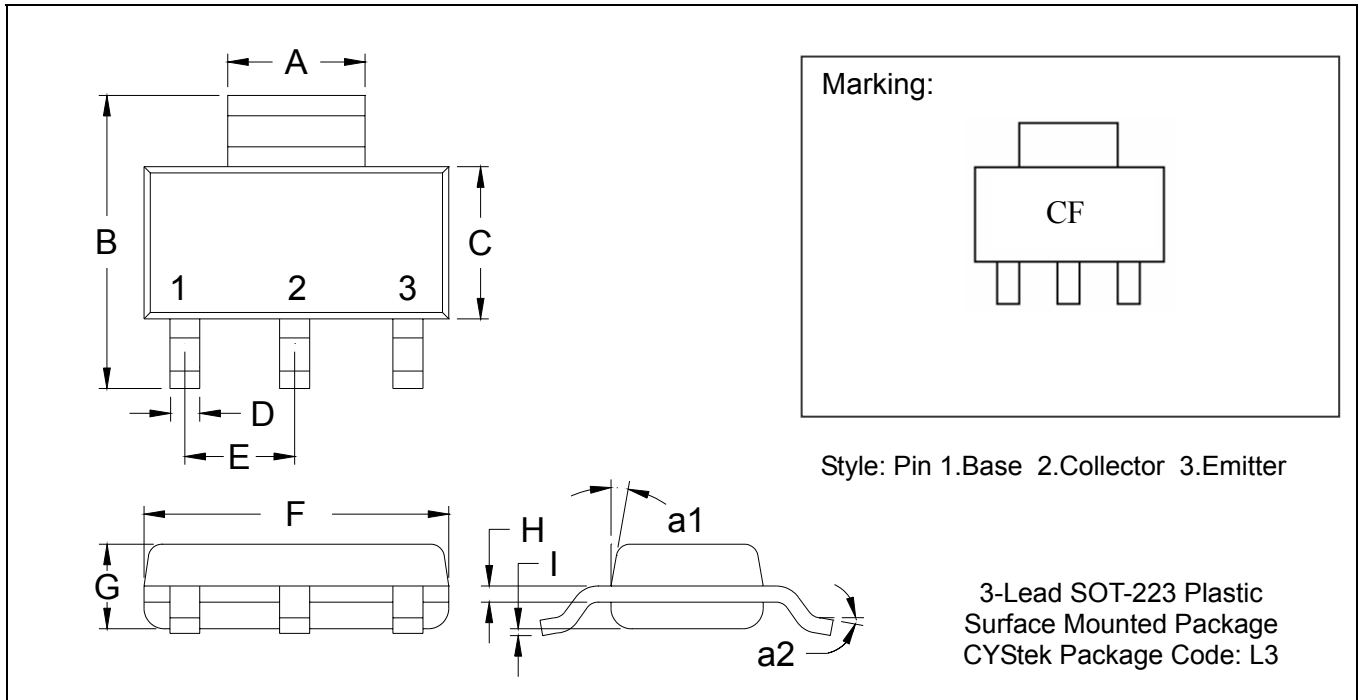
Saturation voltage vs Collector current



Power Derating Curve



**SOT-223 Dimension**



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1142	0.1220	2.90	3.10	G	0.0551	0.0709	1.40	1.80
B	0.2638	0.2874	6.70	7.30	H	0.0098	0.0138	0.25	0.35
C	0.1299	0.1457	3.30	3.70	I	0.0008	0.0039	0.02	0.10
D	0.0236	0.0315	0.60	0.80	a1	*13°	-	*13°	-
E	*0.0906	-	*2.30	-	a2	0°	10°	0°	10°
F	0.2480	0.2638	6.30	6.70					

Notes: 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: 42 Alloy; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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